

ABSTRACT OF THE DISCLOSURE

A film-forming surface reforming method includes the steps of bringing a gas or an aqueous solution containing ammonia, hydrazine, an amine, an amino compound or a derivative thereof into contact with the film-forming surface before an insulating film is formed on the film-forming surface, and bringing a gas or an aqueous solution containing hydrogen peroxide, ozone, oxygen, nitric acid, sulfuric acid or a derivative thereof into contact with the film-forming surface.